

2SC5244, 2SC5244A

Silicon NPN triple diffusion mesa type

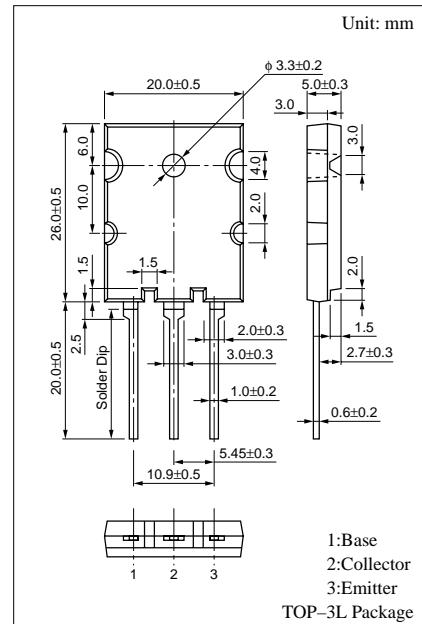
For horizontal deflection output

■ Features

- High breakdown voltage, and high reliability through the use of a glass passivation layer
- High-speed switching
- Wide area of safe operation (ASO)

■ Absolute Maximum Ratings ($T_C=25^\circ\text{C}$)

Parameter		Symbol	Ratings	Unit
Collector to base voltage	2SC5244	V_{CBO}	1500	V
	2SC5244A		1600	
Collector to emitter voltage	2SC5244	V_{CES}	1500	V
	2SC5244A		1600	
Emitter to base voltage		V_{EBO}	6	V
Peak collector current		I_{CP}	20	A
Collector current		I_{C}	30	A
Collector power dissipation	$T_C=25^\circ\text{C}$	P_{C}	200	W
	$T_a=25^\circ\text{C}$		3.5	
Junction temperature		T_j	150	$^\circ\text{C}$
Storage temperature		T_{stg}	-55 to +150	$^\circ\text{C}$



■ Electrical Characteristics ($T_C=25^\circ\text{C}$)

Parameter		Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	2SC5244	I_{CBO}	$V_{\text{CB}} = 1500\text{V}, I_{\text{E}} = 0$			1	mA
	2SC5244A		$V_{\text{CB}} = 1600\text{V}, I_{\text{E}} = 0$			1	
Emitter cutoff current		I_{EBO}	$V_{\text{EB}} = 5\text{V}, I_{\text{C}} = 0$			50	μA
Forward current transfer ratio		h_{FE}	$V_{\text{CE}} = 5\text{V}, I_{\text{C}} = 10\text{A}$	5		12	
Collector to emitter saturation voltage		$V_{\text{CE(sat)}}$	$I_{\text{C}} = 10\text{A}, I_{\text{B}} = 2.8\text{A}$			3	V
Base to emitter saturation voltage		$V_{\text{BE(sat)}}$	$I_{\text{C}} = 10\text{A}, I_{\text{B}} = 2.8\text{A}$			1.5	V
Transition frequency		f_T	$V_{\text{CE}} = 10\text{V}, I_{\text{C}} = 0.1\text{A}, f = 0.5\text{MHz}$		3		MHz
Storage time		t_{stg}	$I_{\text{C}} = 12\text{A}, I_{\text{B1}} = 2.4\text{A}, I_{\text{B2}} = -4.8\text{A},$ Resistance loaded		1.5	2.5	μs
Fall time		t_f			0.12	0.2	μs

